



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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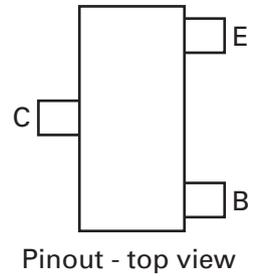
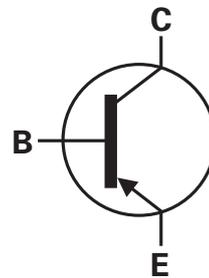
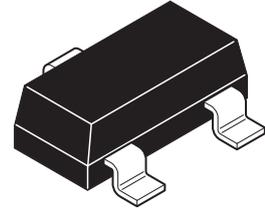
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### Absolute maximum ratings

Parameter	Symbol	Value	Unit
Collector-base voltage	$V_{CBO}$	-220	V
Collector-emitter voltage	$V_{CEO}$	-200	V
Emitter-base voltage	$V_{EBO}$	-5	V
Peak pulse current	$I_{CM}$	-1	A
Continuous collector current	$I_C$	-0.3	A
Base current	$I_B$	-200	mA
Power dissipation at $T_{amb}=25^{\circ}C$	$P_{tot}$	500	mW
Operating and storage temperature range	$T_J; T_{stg}$	-55 to +150	$^{\circ}C$

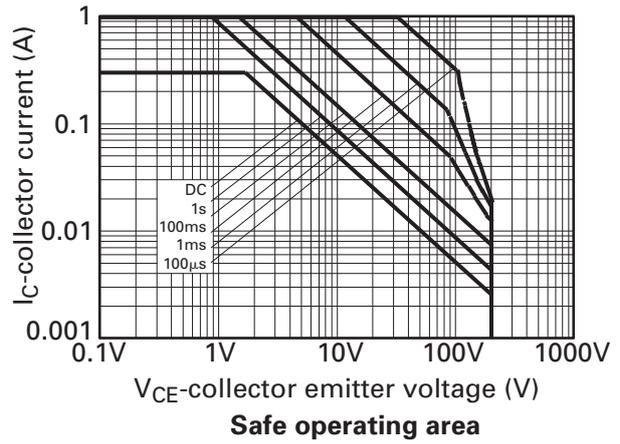
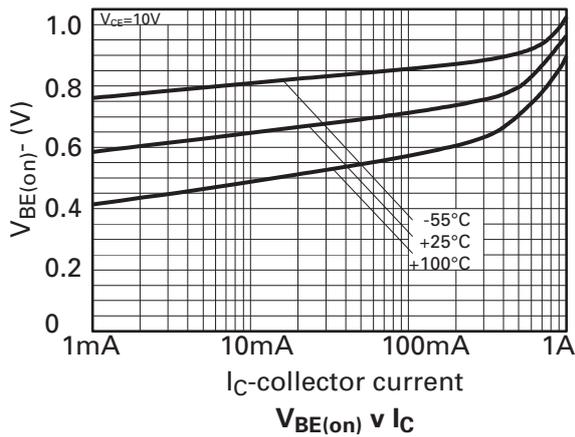
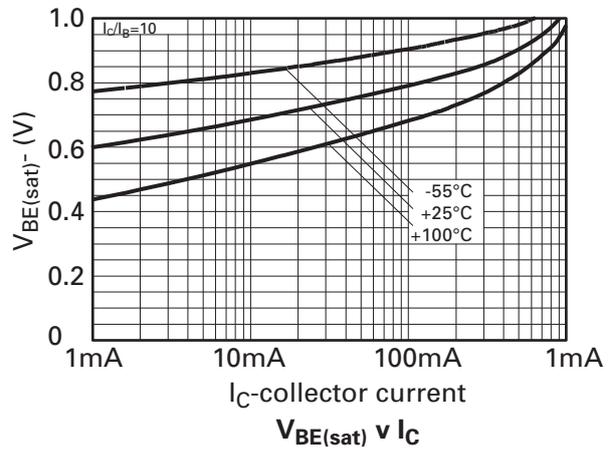
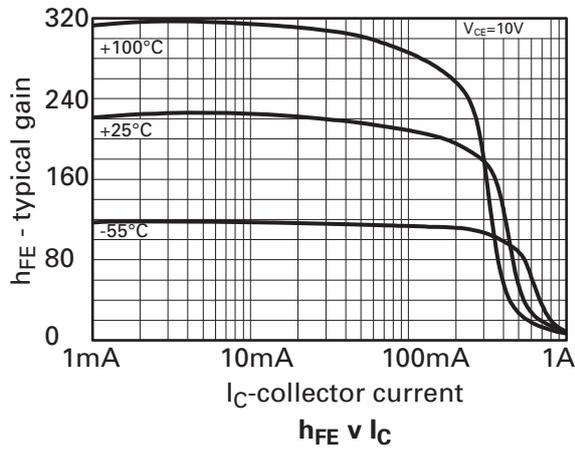
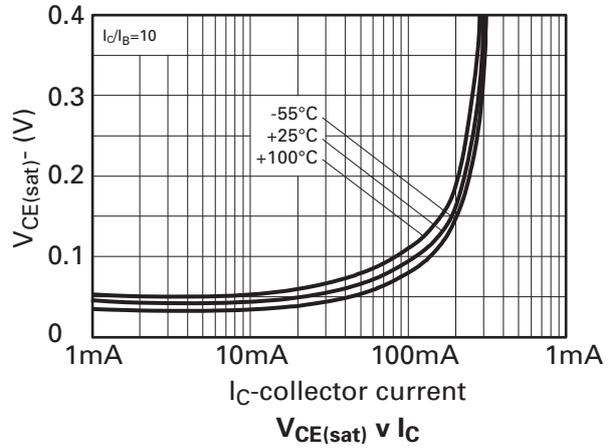
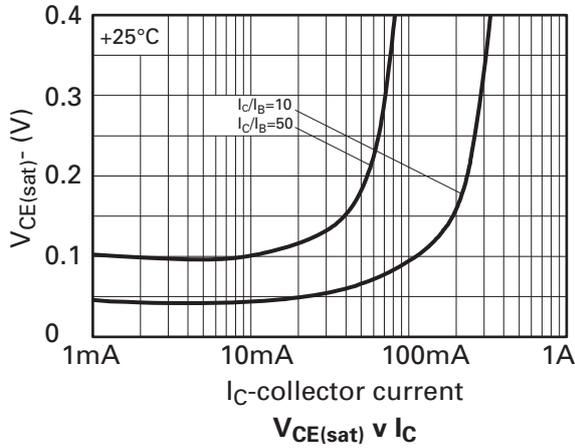
**Electrical characteristics (T<sub>amb</sub> = 25°C)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	-220			V	I <sub>C</sub> =-100μA
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	-200			V	I <sub>C</sub> =-10mA <sup>(*)</sup>
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	-5			V	I <sub>E</sub> =-100μA
Collector cut-off current	I <sub>CBO</sub>			-100	nA	V <sub>CB</sub> =-200V
Emitter cut-off current	I <sub>EBO</sub>			-100	nA	V <sub>EB</sub> =-4V
Collector-emitter cut-off current	I <sub>CES</sub>			-100	nA	V <sub>CE</sub> =-200V
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>			-0.2 -0.35	V V	I <sub>C</sub> =-100mA, I <sub>B</sub> =-10mA, I <sub>B</sub> =-250mA, I <sub>B</sub> =-25mA <sup>(*)</sup>
Base-emitter saturation voltage	V <sub>BE(sat)</sub>			-1.0	V	I <sub>C</sub> =-250mA, I <sub>B</sub> =-25mA <sup>(*)</sup>
Base-emitter turn-on voltage	V <sub>BE(on)</sub>			-0.9	V	I <sub>C</sub> =-250mA, V <sub>CE</sub> =-10V <sup>(*)</sup>
Static forward current transfer ratio	h <sub>FE</sub>	100 100 85 35		300		I <sub>C</sub> =-1mA, V <sub>CE</sub> =-10V I <sub>C</sub> =-100mA, V <sub>CE</sub> =-10V <sup>(*)</sup> I <sub>C</sub> =-250mA, V <sub>CE</sub> =-10V <sup>(*)</sup> I <sub>C</sub> =-400mA, V <sub>CE</sub> =-10V <sup>(*)</sup>
Transition frequency	f <sub>T</sub>	150			MHz	I <sub>C</sub> =-50mA, V <sub>CE</sub> =-10V, f=100MHz
Output capacitance	C <sub>obo</sub>			10	pF	V <sub>CB</sub> =-10V, f=1MHz
Switching times	td tr ts tf		22 19 472 70		ns	I <sub>C</sub> =-200mA, V <sub>CC</sub> =-80V I <sub>b1</sub> =I <sub>b2</sub> =-20mA
Switching times	td tr ts tf		44 31 665 76		ns	I <sub>C</sub> =-100mA, V <sub>CC</sub> =-80V I <sub>b1</sub> =I <sub>b2</sub> =-10mA

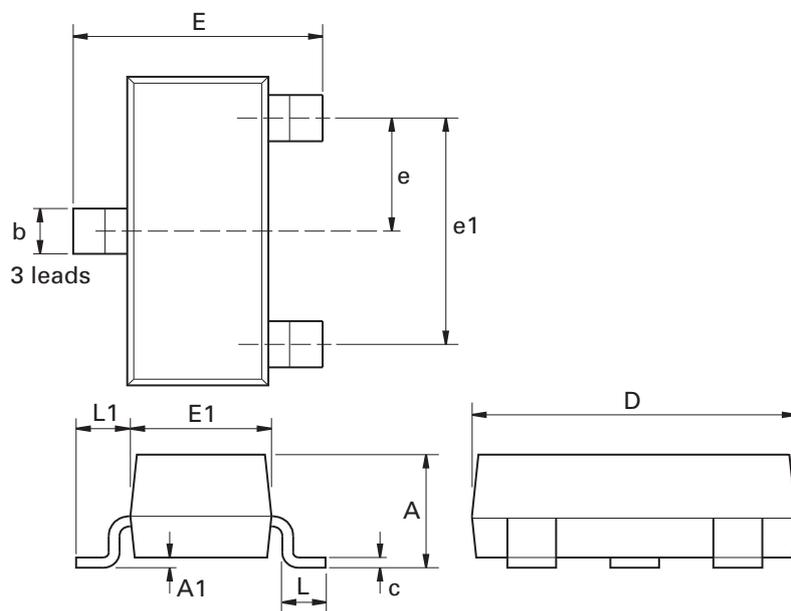
**NOTES:**

(\*) Measured under pulsed conditions. Pulse width = 300μs. Duty cycle ≤2%.

Typical characteristics



Package outline - SOT23



Dim.	Millimeters		Inches		Dim.	Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	-	1.12	-	0.044	e1	1.90 NOM		0.075 NOM	
A1	0.01	0.10	0.0004	0.004	E	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
c	0.085	0.20	0.003	0.008	L	0.25	0.60	0.0098	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
e	0.95 NOM		0.037 NOM		-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches